

TSM180N03CS RLG

TSM180N03CS RLG Information

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Part Number TSM180N03CS RLG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET, SINGLE, N-CHANNEL, TRENC

Package 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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TSM180N03CS RLG Specifications

Manufacturer Part Number TSM180N03CS RLG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 345pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ) Mounting Type		
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Input Capacitance (Ciss) (Max) @ Vds 345pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ)	Gate Charge (Qg) (Max) @ Vgs	14nC @ 4.5V
FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	345pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 18 mOhm @ 8A, 10V Operating Temperature 150°C (TJ)	FET Feature	-
Operating Temperature 150°C (TJ)	Power Dissipation (Max)	2.5W (Tc)
	Rds On (Max) @ Id, Vgs	18 mOhm @ 8A, 10V
Mounting Type	Operating Temperature	150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package 8-SOP	Supplier Device Package	8-SOP
Package / Case 8-SOIC (0.154", 3.90mm Width)	Package / Case	8-SOIC (0.154", 3.90mm Width)
Report errors?		Report errors?

TSM180N03CS RLG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM180N03CS RLG Payment Methods



















TSM180N03CS RLG Shipping Methods













If you have any question about TSM180N03CS RLG, please do not hesitate to contact us!

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